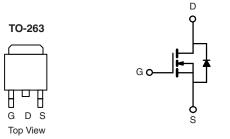


Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0018				
I _D (A)	120				
Configuration	Single				



N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualifiedd
- 100 % R_a and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



	ORDERING INFORMATION	
	Package	TO-263
ſ	Lead (Pb)-free and Halogen-free	SQM120N04-1m8-GF3

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Currenta	T _C = 25 °C	1	120	А	
Continuous Drain Current	T _C = 125 °C	- I _D	120		
Continuous Source Current (Diode Conduct	tion) ^a	I _S	120		
Pulsed Drain Current ^b	I _{DM}	480			
Single Pulse Avalanche Current		I _{AS}	85		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	361	mJ	
Maximum Bayyar Dissination	T _C = 25 °C	D	375	W	
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	125	VV	
Operating Junction and Storage Temperatu	re Range	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient P	PCB Mount ^c	R_{thJA}	40	°C/W		
Junction-to-Case (Drain)		R_{thJC}	0.4	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

SQM120N04-1m8

Vishay Siliconix



SPECIFICATIONS ($T_C = 25 ^{\circ}C_{\odot}$, unless otherv	vise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static						•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		40	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3.0	3.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	250	1	
On-State Drain Currenta	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	120	-	-	Α	
		V _{GS} = 10 V	I _D = 30 A	-	0.0015	0.0018		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0028	Ω	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0034		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 30 A		-	198	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}				13 880	17 350		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	5720	7150	pF	
Reverse Transfer Capacitance	C _{rss}]		-	840	1050		
Total Gate Charge ^c	Qg			-	206	310		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_{D} = 120 \text{ A}$	-	50	-	nC	
Gate-Drain Charge ^c	Q _{gd}	1		-	44	-		
Gate Resistance	R _g		f = 1 MHz	0.57	1.14	1.71	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	26	39		
Rise Time ^c	t _r	V_{DD} = 20 V, R_L = 0.17 Ω $I_D \cong$ 120 A, V_{GEN} = 10 V, R_g = 1 Ω		-	21	32	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	68	102		
Fall Time ^c	t _f			-	12	18		
Source-Drain Diode Ratings and Char	acteristics ^b	•				•		
Pulsed Current ^a	I _{SM}			-	-	480	Α	
Forward Voltage	V_{SD}	I _F = 80 A, V _{GS} = 0		-	0.86	1.5	V	

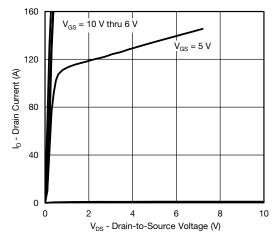
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

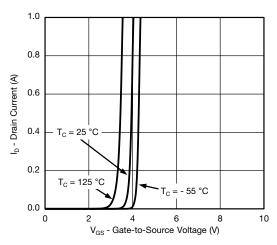
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



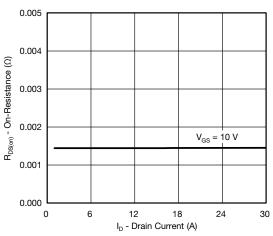
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



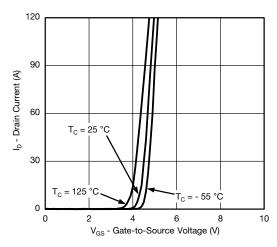
Output Characteristics



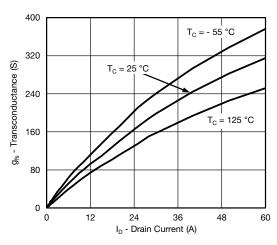
Transfer Characteristics



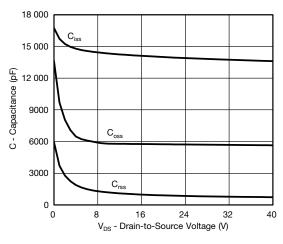
On-Resistance vs. Drain Current



Transfer Characteristics



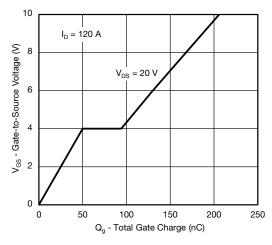
Transconductance



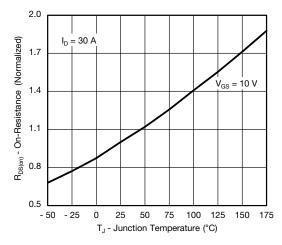
Capacitance



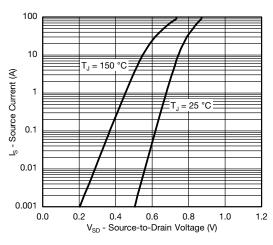
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



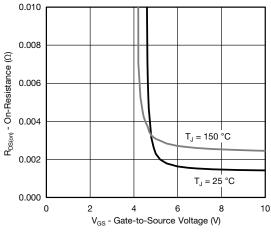
Gate Charge



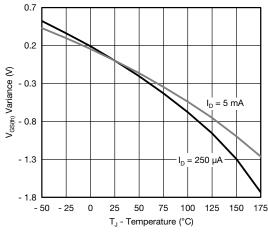
On-Resistance vs. Junction Temperature



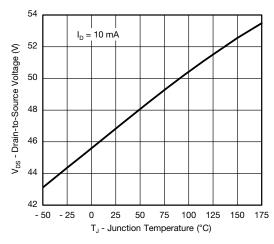
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

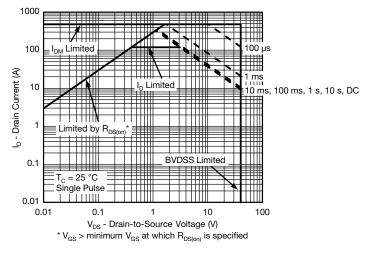


Threshold Voltage

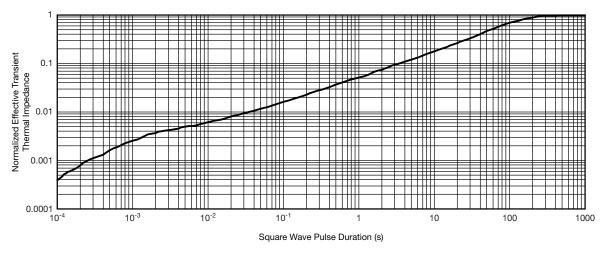


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



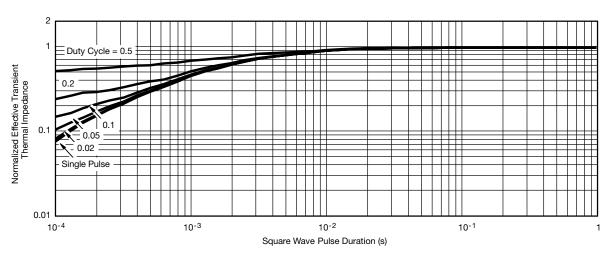
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

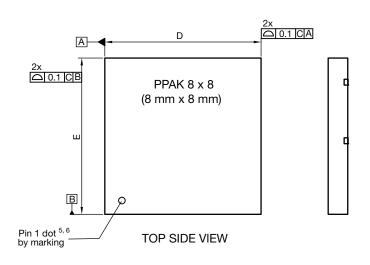
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

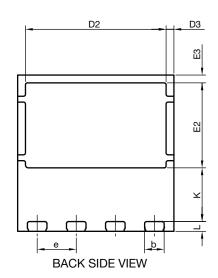
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

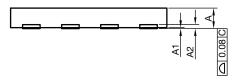
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PowerPAK® 8 x 8 Case Outline







DIM.	MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	0.95	1.00	1.05	0.037	0.039	0.041
A1	0.00	-	0.05	0.000	-	0.002
A2		020 ref.			0.008 ref.	
b	0.95	1.00	1.05	0.037	0.039	0.041
D	7.90	8.00	8.10	0.311	0.315	0.319
D2	7.10	7.20	7.30	0.280	0.283	0.287
D3	0.40 BSC			0.016 BSC		
е	2.00 BSC			0.079 BSC		
Е	7.90	8.00	8.10	0.311	0.315	0.319
E2	4.30	4.35	4.40	0.169	0.171	0.173
E3	0.40 BSC				0.016 BSC	
K	2.75 BSC				0.108 BSC	
L	0.45	0.50	0.55	0.018	0.020	0.022
N ⁽³⁾		8		8		

Notes

- (1) Use millimeters as the primary measurement
- (2) Dimensioning and tolerances conform to ASME Y14.5 M 1994
- (3) N is the number of terminals
- (4) The pin 1 identifier must be existed on the top surface of the package by using indentation mark or other feature of package body
- (5) Exact shape and size of this feature is optional

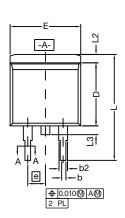
ECN: E20-0518-Rev. B, 28-Sep-2020

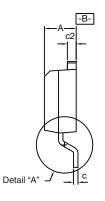
DWG: 6041

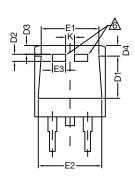
Revision: 28-Sep-2020 1 Document Number: 67859



TO-263 (D²PAK): 3-LEAD

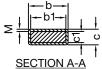








DETAIL A (ROTATED 90°)



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≥‡	<i>্লালা</i> চ	ပ
S	FCTION A-A	\Box

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

		INC	HES	MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
	Α	0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.038 0.042 0		1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	=	
	E2 0.355		0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100) BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

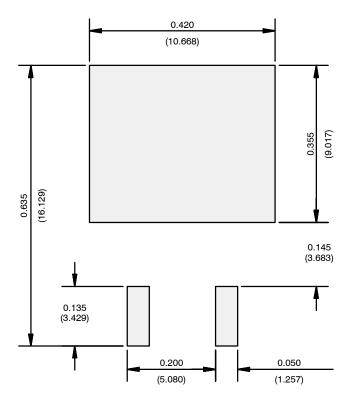
DWG: 5843

Revison: 30-Sep-13 Document Number: 71198





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

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